

## CMOS Quad 2-Input NAND Schmitt Triggers

High-Voltage Types (20 Volt Rating)

■ CD4093B consists of four Schmitt-trigger circuits. Each circuit functions as a two-input NAND gate with Schmitt-trigger action on both inputs. The gate switches at different points for positive- and negative-going signals. The difference between the positive voltage ( $V_P$ ) and the negative voltage ( $V_N$ ) is defined as hysteresis voltage ( $V_H$ ) (see Fig. 2).

The CD4093 types are supplied in a 14-lead hermetic dual-in-line ceramic package (F suffix), 14-lead dual-in-line plastic package (E suffix), 14-lead dual-in-line plastic small-outline package (M), and in chip form (H suffix). Add the suffix 96 to the M package for tape and reel.

### MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, ( $V_{DD}$ )	-0.5V to +20V
Voltages referenced to $V_{SS}$ Terminal	
INPUT VOLTAGE RANGE, ALL INPUTS	-0.5V to $V_{DD} + 0.5V$
DC INPUT CURRENT, ANY ONE INPUT	$\pm 10\text{mA}$
PACKAGE THERMAL IMPEDANCE, $\theta_{JA}$ (See Note 1):	
E package	80°C/W
M package	86°C/W
DEVICE DISSIPATION PER OUTPUT TRANSISTOR	
FOR $T_A$ = FULL PACKAGE-TEMPERATURE RANGE (All Package Types)	100mW
OPERATING-TEMPERATURE RANGE ( $T_A$ )	-55°C to +125°C
STORAGE TEMPERATURE RANGE ( $T_{stg}$ )	-65°C to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 $\pm$ 1/32 inch (1.59 $\pm$ 0.79mm) from case for 10s max	+265°C

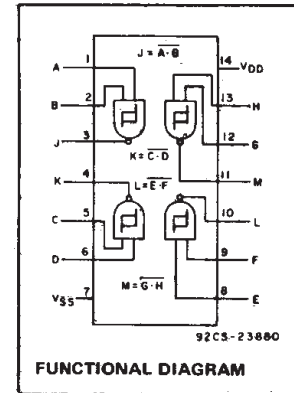
NOTE 1: Package thermal impedance is calculated in accordance with JESD 51.

### Features:

- Schmitt-trigger action on each input with no external components
- Hysteresis voltage typically 0.9 V at  $V_{DD} = 5\text{ V}$  and 2.3 V at  $V_{DD} = 10\text{ V}$
- Noise immunity greater than 50%
- No limit on input rise and fall times
- Standardized, symmetrical output characteristics
- 100% tested for quiescent current at 20 V
- Maximum input current of 1  $\mu\text{A}$  at 18 V over full package-temperature range, 100 nA at 18 V and 25°C
- 5-V, 10-V, and 15-V parametric ratings
- Meets all requirements of JEDEC Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"

### Applications:

- Wave and pulse shapers
- High-noise-environment systems
- Monostable multivibrators
- Astable multivibrators
- NAND logic



### RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges.

CHARACTERISTIC	MIN.	MAX.	UNITS
Supply Voltage Range ( $T_A$ = Full Package Temp. Range)	3	18	V



\* ALL INPUTS PROTECTED BY CMOS PROTECTION NETWORK

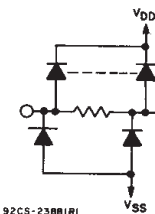


Fig. 1 - Logic diagram-1 of 4 Schmitt triggers.

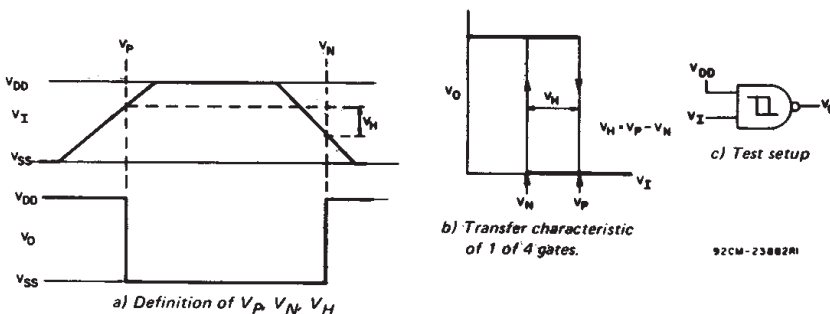


Fig. 2 - Hysteresis definition, characteristic, and test setup.

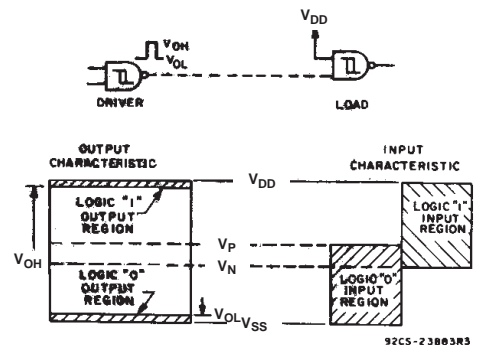


Fig. 3 - Input and output characteristics.

# CD4093B Types

## STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
	V <sub>O</sub> (V)	V <sub>IN</sub> (V)	V <sub>DD</sub> (V)	-55	-40	+85	+125	+25			
								MIN.	TYP.	MAX.	
Quiescent Device Current, I <sub>DD</sub> Max.	-	0.5	5	1	1	30	30	-	0.02	1	μA
	-	0.10	10	2	2	60	60	-	0.02	2	
	-	0.15	15	4	4	120	120	-	0.02	4	
	-	0.20	20	20	20	600	600	-	0.04	20	
Positive Trigger Threshold Voltage V <sub>p</sub> Min.	-	a	5	2.2	2.2	2.2	2.2	2.2	2.9	-	V
	-	a	10	4.6	4.6	4.6	4.6	4.6	5.9	-	
	-	a	15	6.8	6.8	6.8	6.8	6.8	8.8	-	
	-	b	5	2.6	2.6	2.6	2.6	2.6	3.3	-	
	-	b	10	5.6	5.6	5.6	5.6	5.6	7	-	
	-	b	15	6.3	6.3	6.3	6.3	6.3	9.4	-	
V <sub>p</sub> Max.	-	a	5	3.6	3.6	3.6	3.6	-	2.9	3.6	V
	-	a	10	7.1	7.1	7.1	7.1	-	5.9	7.1	
	-	a	15	10.8	10.8	10.8	10.8	-	8.8	10.8	
	-	b	5	4	4	4	4	-	3.3	4	
	-	b	10	8.2	8.2	8.2	8.2	-	7	8.2	
	-	b	15	12.7	12.7	12.7	12.7	-	9.4	12.7	
Negative Trigger Threshold Voltage V <sub>N</sub> Min.	-	a	5	0.9	0.9	0.9	0.9	0.9	1.9	-	V
	-	a	10	2.5	2.5	2.5	2.5	2.5	3.9	-	
	-	a	15	4	4	4	4	4	5.8	-	
	-	b	5	1.4	1.4	1.4	1.4	1.4	2.3	-	
	-	b	10	3.4	3.4	3.4	3.4	3.4	5.1	-	
	-	b	15	4.8	4.8	4.8	4.8	4.8	7.3	-	
V <sub>N</sub> Max.	-	a	5	2.8	2.8	2.8	2.8	-	1.9	2.8	V
	-	a	10	5.2	5.2	5.2	5.2	-	3.9	5.2	
	-	a	15	7.4	7.4	7.4	7.4	-	5.8	7.4	
	-	b	5	3.2	3.2	3.2	3.2	-	2.3	3.2	
	-	b	10	6.6	6.6	6.6	6.6	-	5.1	6.6	
	-	b	15	9.6	9.6	9.6	9.6	-	7.3	9.6	
Hysteresis Voltage V <sub>H</sub> Min.	-	a	5	0.3	0.3	0.3	0.3	0.3	0.9	-	V
	-	a	10	1.2	1.2	1.2	1.2	1.2	2.3	-	
	-	a	15	1.6	1.6	1.6	1.6	1.6	3.5	-	
	-	b	5	0.3	0.3	0.3	0.3	0.3	0.9	-	
	-	b	10	1.2	1.2	1.2	1.2	1.2	2.3	-	
	-	b	15	1.6	1.6	1.6	1.6	1.6	3.5	-	
V <sub>H</sub> Max.	-	a	5	1.6	1.6	1.6	1.6	-	0.9	1.6	V
	-	a	10	3.4	3.4	3.4	3.4	-	2.3	3.4	
	-	a	15	5	5	5	5	-	3.5	5	
	-	b	5	1.6	1.6	1.6	1.6	-	0.9	1.6	
	-	b	10	3.4	3.4	3.4	3.4	-	2.3	3.4	
	-	b	15	5	5	5	5	-	3.5	5	

<sup>a</sup> Input on terminals 1,5,8,12 or 2,6,9,13; other inputs to V<sub>DD</sub>.

<sup>b</sup> Input on terminals 1 and 2, 5 and 6, 8 and 9, or 12 and 13; other inputs to V<sub>DD</sub>.

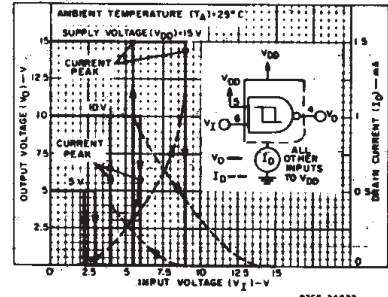


Fig. 4 - Typical current and voltage transfer characteristics.

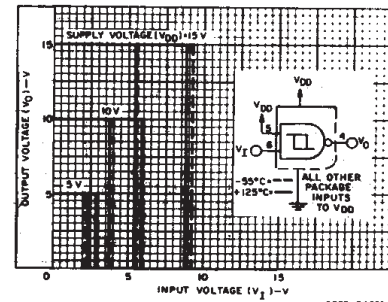


Fig. 5 - Typical voltage transfer characteristics as a function of temperature.

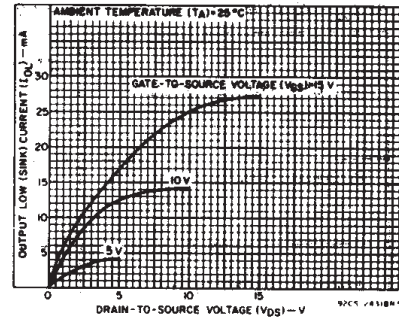


Fig. 6 - Typical output low (sink) current characteristics.

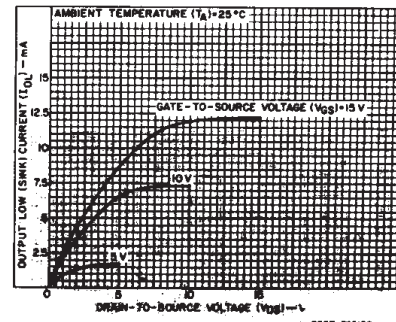


Fig. 7 - Minimum output low (sink) current characteristics.

# CD4093B Types

## STATIC ELECTRICAL CHARACTERISTICS (CONT'D)

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
	V <sub>O</sub> (V)	V <sub>IN</sub> (V)	V <sub>DD</sub> (V)	-55	-40	+85	+125	+25			
								MIN.	TYP.	MAX.	
Output Low (Sink) Current, I <sub>OL</sub> Min.	0.4	0.5	5	0.64	0.61	0.42	0.36	0.51	1	-	mA
	0.5	0.10	10	1.6	1.5	1.1	0.9	1.3	2.6	-	
	1.5	0.15	15	4.2	4	2.8	2.4	3.4	6.8	-	
Output High (Source) Current, I <sub>OH</sub> Min.	4.6	0.5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	-	mA
	2.5	0.5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	-	
	9.5	0.10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	-	
	13.5	0.15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	-	
Output Voltage Low-Level, V <sub>OL</sub> Max.	-	0.5	5	0.05			-	0	0.05	-	V
	-	0.10	10	0.05			-	0	0.05	-	
	-	0.15	15	0.05			-	0	0.05	-	
Output Voltage High-Level, V <sub>OH</sub> Min.	-	0.5	5	4.95			4.95	5	-	-	V
	-	0.10	10	9.95			9.95	10	-	-	
	-	0.15	15	14.95			14.95	-	-	-	
Input Current, I <sub>IN</sub> Max.	-	0.18	18	±0.1	±0.1	±1	±1	-	±10 <sup>-5</sup>	±0.1	μA

## DYNAMIC ELECTRICAL CHARACTERISTICS

At T<sub>A</sub> = 25°C; Input t<sub>r</sub>, t<sub>f</sub> = 20 ns, C<sub>L</sub> = 50 pF, R<sub>L</sub> = 200kΩ

CHARACTERISTIC	TEST CONDITIONS	LIMITS			UNITS
		V <sub>DD</sub> VOLTS	TYP.	MAX.	
Propagation Delay Time: t <sub>PHL</sub> t <sub>PLH</sub>		5	190	380	ns
		10	90	180	
		15	65	130	
Transition Time, t <sub>THL</sub> t <sub>TLH</sub>		5	100	200	ns
		10	50	100	
		15	40	80	
Input Capacitance, C <sub>IN</sub>	Any Input		5	7.5	pF

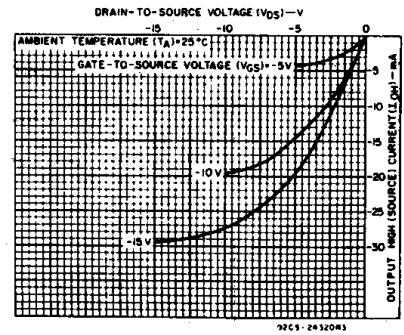


Fig. 8 - Typical output high (source) current characteristics.

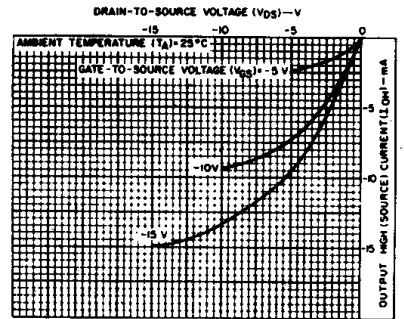


Fig. 9 - Minimum output high (source) current characteristics.

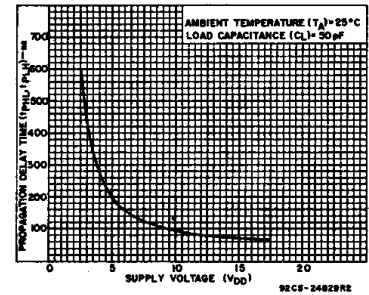


Fig. 10 - Typical propagation delay time vs. supply voltage.

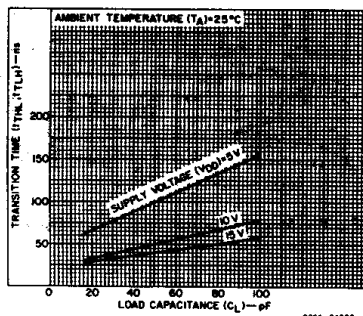


Fig. 11 - Typical transition time vs. load capacitance.

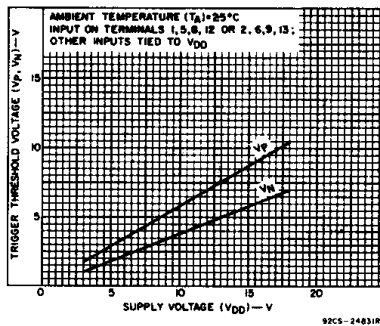


Fig. 12 - Typical trigger threshold voltage vs. V<sub>DD</sub>.

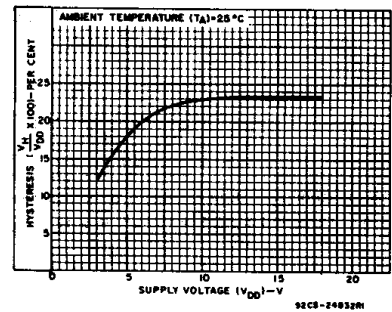


Fig. 13 - Typical per cent hysteresis vs. supply voltage.

# CD4093B Types



Fig. 14 - Typical power dissipation vs. frequency characteristics.

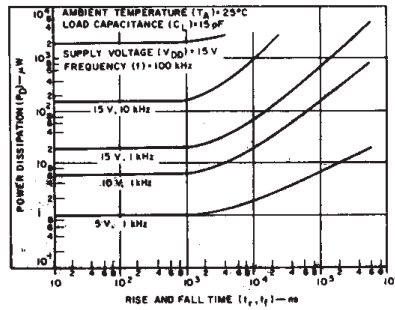


Fig. 15 - Typical power dissipation vs. rise and fall times.

## APPLICATIONS



Fig. 16 - Wave shaper.



Fig. 17 - Monostable multivibrator.

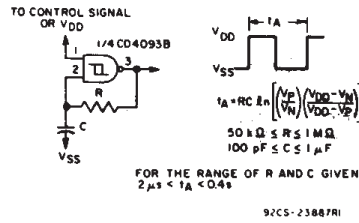


Fig. 18 - Astable multivibrator.

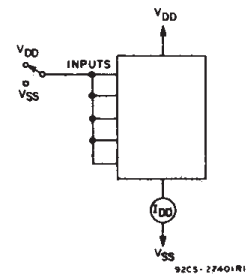


Fig. 19 - Quiescent device current test circuit.

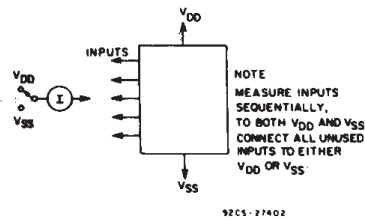
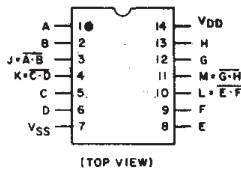


Fig. 20 - Input current test circuit.



TERMINAL ASSIGNMENT

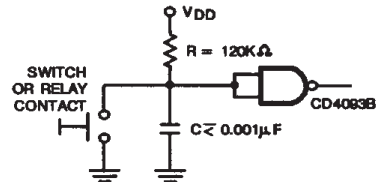


Fig. 21 - Contact Debouncer

## IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.